
2SK1070

Silicon N-Channel Junction FET

HITACHI

ADE-208-1175 (Z)

1st. Edition

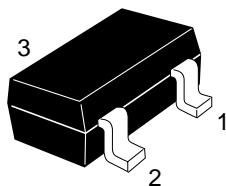
Mar. 2001

Application

Low frequency / High frequency amplifier

Outline

MPAK



- 1. Drain
- 2. Source
- 3. Gate

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|---------------------------|-----------|-------------|------|
| Gate to drain voltage | V_{GDO} | -22 | V |
| Gate to source voltage | V_{GSO} | -22 | V |
| Drain current | I_D | 50 | mA |
| Gate current | I_G | 10 | mA |
| Channel power dissipation | Pch | 150 | mW |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Electrical Characteristics (Ta = 25°C)

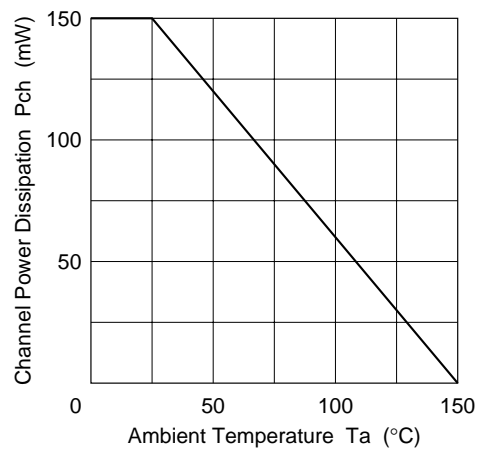
| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|----------------------------------|----------------|-----|-----|------|------|---|
| Gate cutoff current | I_{GSS} | — | — | -10 | nA | $V_{GS} = -15\text{ V}$, $V_{DS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | -22 | — | — | V | $I_G = -10\text{ }\mu\text{A}$, $V_{DS} = 0$ |
| Drain current | I_{DSS}^{*1} | 6 | — | 40 | mA | $V_{DS} = 5\text{ V}$, $V_{GS} = 0$, Pulse test |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 0 | — | -2.5 | V | $V_{DS} = 5\text{ V}$, $I_D = 10\text{ }\mu\text{A}$ |
| Forward transfer admittance | $ y_{fs} $ | 20 | 30 | — | mS | $V_{DS} = 5\text{ V}$, $V_{GS} = 0$, $f = 1\text{ kHz}$ |
| Input capacitance | Ciss | — | 9 | — | pF | $V_{DS} = 5\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$ |

Note: 1. The 2SK1070 is grouped by I_{DSS} as follows.

| Grade | B | C | D | E |
|-----------|---------|----------|----------|----------|
| Mark | PIB | PIC | PID | PIE |
| I_{DSS} | 6 to 14 | 12 to 22 | 18 to 30 | 27 to 40 |

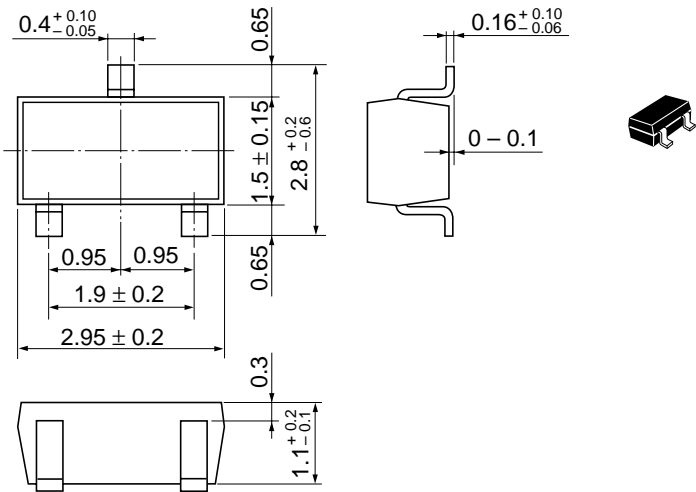
See characteristic curves of 2SK435.

Maximum Channel Dissipation Curve



Package Dimensions

As of January, 2001
Unit: mm



| | |
|------------------------|----------|
| Hitachi Code | MPAK |
| JEDEC | — |
| EIAJ | Conforms |
| Mass (reference value) | 0.011 g |

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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| URL | NorthAmerica | : http://semiconductor.hitachi.com/ |
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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